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### AMD Xilinx - XC2S100-5FG456C Datasheet



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#### Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

#### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Obsolete
Number of LABs/CLBs	600
Number of Logic Elements/Cells	2700
Total RAM Bits	40960
Number of I/O	196
Number of Gates	100000
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	456-BBGA
Supplier Device Package	456-FBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc2s100-5fg456c

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

drivers are disabled. Maintaining a valid logic level in this way helps eliminate bus chatter.

Because the weak-keeper circuit uses the IOB input buffer to monitor the input level, an appropriate  $V_{REF}$  voltage must be provided if the signaling standard requires one. The provision of this voltage must comply with the I/O banking rules.

# I/O Banking

Some of the I/O standards described above require  $V_{CCO}$  and/or  $V_{REF}$  voltages. These voltages are externally connected to device pins that serve groups of IOBs, called banks. Consequently, restrictions exist about which I/O standards can be combined within a given bank.

Eight I/O banks result from separating each edge of the FPGA into two banks (see Figure 3). Each bank has multiple  $V_{CCO}$  pins which must be connected to the same voltage. Voltage is determined by the output standards in use.



DS001\_03\_060100

Figure 3: Spartan-II I/O Banks

Within a bank, output standards may be mixed only if they use the same  $V_{CCO}$ . Compatible standards are shown in Table 4. GTL and GTL+ appear under all voltages because their open-drain outputs do not depend on  $V_{CCO}$ .

### Table 4: Compatible Output Standards

V <sub>cco</sub>	Compatible Standards
3.3V	PCI, LVTTL, SSTL3 I, SSTL3 II, CTT, AGP, GTL, GTL+
2.5V	SSTL2 I, SSTL2 II, LVCMOS2, GTL, GTL+
1.5V	HSTL I, HSTL III, HSTL IV, GTL, GTL+

Some input standards require a user-supplied threshold voltage,  $V_{\text{REF}}$  In this case, certain user-I/O pins are

automatically configured as inputs for the V<sub>REF</sub> voltage. About one in six of the I/O pins in the bank assume this role.

 $V_{\text{REF}}$  pins within a bank are interconnected internally and consequently only one  $V_{\text{REF}}$  voltage can be used within each bank. All  $V_{\text{REF}}$  pins in the bank, however, must be connected to the external voltage source for correct operation.

In a bank, inputs requiring V<sub>REF</sub> can be mixed with those that do not but only one V<sub>REF</sub> voltage may be used within a bank. Input buffers that use V<sub>REF</sub> are not 5V tolerant. LVTTL, LVCMOS2, and PCI are 5V tolerant. The V<sub>CCO</sub> and V<sub>REF</sub> pins for each bank appear in the device pinout tables.

Within a given package, the number of V<sub>REF</sub> and V<sub>CCO</sub> pins can vary depending on the size of device. In larger devices, more I/O pins convert to V<sub>REF</sub> pins. Since these are always a superset of the V<sub>REF</sub> pins used for smaller devices, it is possible to design a PCB that permits migration to a larger device. All V<sub>REF</sub> pins for the largest device anticipated must be connected to the V<sub>REF</sub> voltage, and not used for I/O.

Independent Banks Available

Package	VQ100	CS144	FG256
	PQ208	TQ144	FG456
Independent Banks	1	4	8

# **Configurable Logic Block**

The basic building block of the Spartan-II FPGA CLB is the logic cell (LC). An LC includes a 4-input function generator, carry logic, and storage element. Output from the function generator in each LC drives the CLB output and the D input of the flip-flop. Each Spartan-II FPGA CLB contains four LCs, organized in two similar slices; a single slice is shown in Figure 4.

In addition to the four basic LCs, the Spartan-II FPGA CLB contains logic that combines function generators to provide functions of five or six inputs.

# Look-Up Tables

Spartan-II FPGA function generators are implemented as 4-input look-up tables (LUTs). In addition to operating as a function generator, each LUT can provide a 16 x 1-bit synchronous RAM. Furthermore, the two LUTs within a slice can be combined to create a 16 x 2-bit or 32 x 1-bit synchronous RAM, or a 16 x 1-bit dual-port synchronous RAM.

The Spartan-II FPGA LUT can also provide a 16-bit shift register that is ideal for capturing high-speed or burst-mode data. This mode can also be used to store data in applications such as Digital Signal Processing. Boundary-scan operation is independent of individual IOB configurations, and unaffected by package type. All IOBs, including unbonded ones, are treated as independent 3-state bidirectional pins in a single scan chain. Retention of the bidirectional test capability after configuration facilitates the testing of external interconnections.

Table 7 lists the boundary-scan instructions supported in Spartan-II FPGAs. Internal signals can be captured during EXTEST by connecting them to unbonded or unused IOBs. They may also be connected to the unused outputs of IOBs defined as unidirectional input pins.

Boundary-Scan Command	Binary Code[4:0]	Description
EXTEST	00000	Enables boundary-scan EXTEST operation
SAMPLE	00001	Enables boundary-scan SAMPLE operation
USR1	00010	Access user-defined register 1
USR2	00011	Access user-defined register 2
CFG_OUT	00100	Access the configuration bus for Readback
CFG_IN	00101	Access the configuration bus for Configuration
INTEST	00111	Enables boundary-scan INTEST operation
USRCODE	01000	Enables shifting out USER code
IDCODE	01001	Enables shifting out of ID Code
HIZ	01010	Disables output pins while enabling the Bypass Register
JSTART	01100	Clock the start-up sequence when StartupClk is TCK
BYPASS	11111	Enables BYPASS
RESERVED	All other codes	Xilinx <sup>®</sup> reserved instructions

# Table 7: Boundary-Scan Instructions

The public boundary-scan instructions are available prior to configuration. After configuration, the public instructions remain available together with any USERCODE instructions installed during the configuration. While the SAMPLE and BYPASS instructions are available during configuration, it is recommended that boundary-scan operations not be performed during this transitional period.

In addition to the test instructions outlined above, the boundary-scan circuitry can be used to configure the FPGA, and also to read back the configuration data.

To facilitate internal scan chains, the User Register provides three outputs (Reset, Update, and Shift) that represent the corresponding states in the boundary-scan internal state machine. By default, these operations are synchronized to CCLK. The entire start-up sequence lasts eight cycles, called C0-C7, after which the loaded design is fully functional. The default timing for start-up is shown in the top half of Figure 13. The four operations can be selected to switch on any CCLK cycle C1-C6 through settings in the Xilinx software. Heavy lines show default settings.



Figure 13: Start-Up Waveforms

The bottom half of Figure 13 shows another commonly used version of the start-up timing known as Sync-to-DONE. This version makes the GTS, GSR, and GWE events conditional upon the DONE pin going High. This timing is important for a daisy chain of multiple FPGAs in serial mode, since it ensures that all FPGAs go through start-up together, after all their DONE pins have gone High.

Sync-to-DONE timing is selected by setting the GTS, GSR, and GWE cycles to a value of DONE in the configuration options. This causes these signals to transition one clock cycle after DONE externally transitions High.

## **Serial Modes**

There are two serial configuration modes: In Master Serial mode, the FPGA controls the configuration process by driving CCLK as an output. In Slave Serial mode, the FPGA passively receives CCLK as an input from an external agent (e.g., a microprocessor, CPLD, or second FPGA in master mode) that is controlling the configuration process. In both modes, the FPGA is configured by loading one bit per CCLK cycle. The MSB of each configuration data byte is always written to the DIN pin first.

See Figure 14 for the sequence for loading data into the Spartan-II FPGA serially. This is an expansion of the "Load Configuration Data Frames" block in Figure 11. Note that CS and WRITE normally are not used during serial configuration. To ensure successful loading of the FPGA, do not toggle WRITE with CS Low during serial configuration.





# Master Serial Mode

In Master Serial mode, the CCLK output of the FPGA drives a Xilinx PROM which feeds a serial stream of configuration data to the FPGA's DIN input. Figure 15 shows a Master Serial FPGA configuring a Slave Serial FPGA from a PROM. A Spartan-II device in Master Serial mode should be connected as shown for the device on the left side. Master Serial mode is selected by a <00x> on the mode pins (M0, M1, M2). The PROM RESET pin is driven by INIT, and CE input is driven by DONE. The interface is identical to the slave serial mode except that an oscillator internal to the FPGA is used to generate the configuration clock (CCLK). Any of a number of different frequencies ranging from 4 to 60 MHz can be set using the ConfigRate option in the Xilinx software. On power-up, while the first 60 bytes of the configuration data are being loaded, the CCLK frequency is always 2.5 MHz. This frequency is used until the ConfigRate bits, part of the configuration file, have been loaded into the FPGA, at which point, the frequency changes to the selected ConfigRate. Unless a different frequency is specified in the design, the default ConfigRate is 4 MHz. The frequency of the CCLK signal created by the internal oscillator has a variance of +45%, -30% from the specified value.

Figure 17 shows the timing for Master Serial configuration. The FPGA accepts one bit of configuration data on each rising CCLK edge. After the FPGA has been loaded, the data for the next device in a daisy-chain is presented on the DOUT pin after the rising CCLK edge.



Figure 17: Master Serial Mode Timing

# **Slave Parallel Mode**

The Slave Parallel mode is the fastest configuration option. Byte-wide data is written into the FPGA. A BUSY flag is provided for controlling the flow of data at a clock frequency  $F_{CCNH}$  above 50 MHz.

Figure 18, page 24 shows the connections for two Spartan-II devices using the Slave Parallel mode. Slave Parallel mode is selected by a <011> on the mode pins (M0, M1, M2).

If a configuration file of the format .bit, .rbt, or non-swapped HEX is used for parallel programming, then the most significant bit (i.e. the left-most bit of each configuration byte, as displayed in a text editor) must be routed to the D0 input on the FPGA. The agent controlling configuration is not shown. Typically, a processor, a microcontroller, or CPLD controls the Slave Parallel interface. The controlling agent provides byte-wide configuration data, CCLK, a Chip Select ( $\overline{CS}$ ) signal and a Write signal (WRITE). If BUSY is asserted (High) by the FPGA, the data must be held until BUSY goes Low.

After configuration, the pins of the Slave Parallel port (D0-D7) can be used as additional user I/O. Alternatively, the port may be retained to permit high-speed 8-bit readback. Then data can be read by de-asserting WRITE. See "Readback," page 25.

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# Startup Delay Property

This property, STARTUP\_WAIT, takes on a value of TRUE or FALSE (the default value). When TRUE the Startup Sequence following device configuration is paused at a user-specified point until the DLL locks. <u>XAPP176</u>: *Configuration and Readback of the Spartan-II and Spartan-IIE Families* explains how this can result in delaying the assertion of the DONE pin until the DLL locks.

## **DLL Location Constraints**

The DLLs are distributed such that there is one DLL in each corner of the device. The location constraint LOC, attached to the DLL primitive with the numeric identifier 0, 1, 2, or 3, controls DLL location. The orientation of the four DLLs and their corresponding clock resources appears in Figure 27.

The LOC property uses the following form.

LOC = DLL2



Figure 27: Orientation of DLLs

# **Design Considerations**

Use the following design considerations to avoid pitfalls and improve success designing with Xilinx devices.

# Input Clock

The output clock signal of a DLL, essentially a delayed version of the input clock signal, reflects any instability on the input clock in the output waveform. For this reason the quality of the DLL input clock relates directly to the quality of the output clock waveforms generated by the DLL. The DLL input clock requirements are specified in the "DLL Timing Parameters" section of the data sheet.

In most systems a crystal oscillator generates the system clock. The DLL can be used with any commercially available quartz crystal oscillator. For example, most crystal oscillators produce an output waveform with a frequency tolerance of 100 PPM, meaning 0.01 percent change in the clock period. The DLL operates reliably on an input waveform with a frequency drift of up to 1 ns — orders of magnitude in excess of that needed to support any crystal oscillator in the industry. However, the cycle-to-cycle jitter must be kept to less than 300 ps in the low frequencies and 150 ps for the high frequencies.

## Input Clock Changes

Changing the period of the input clock beyond the maximum drift amount requires a manual reset of the CLKDLL. Failure to reset the DLL will produce an unreliable lock signal and output clock.

It is possible to stop the input clock in a way that has little impact to the DLL. Stopping the clock should be limited to less than approximately 100  $\mu$ s to keep device cooling to a minimum and maintain the validity of the current tap setting. The clock should be stopped during a Low phase, and when restored the full High period should be seen. During this time LOCKED will stay High and remain High when the clock is restored. If these conditions may not be met in the design, apply a manual reset to the DLL after re-starting the input clock, even if the LOCKED signal has not changed.

When the clock is stopped, one to four more clocks will still be observed as the delay line is flushed. When the clock is restarted, the output clocks will not be observed for one to four clocks as the delay line is filled. The most common case will be two or three clocks.

In a similar manner, a phase shift of the input clock is also possible. The phase shift will propagate to the output one to four clocks after the original shift, with no disruption to the CLKDLL control.

# **Output Clocks**

As mentioned earlier in the DLL pin descriptions, some restrictions apply regarding the connectivity of the output pins. The DLL clock outputs can drive an OBUF, a global clock buffer BUFG, or route directly to destination clock pins. The only BUFGs that the DLL clock outputs can drive are the two on the same edge of the device (top or bottom). One DLL output can drive more than one OBUF; however, this adds skew.

Do not use the DLL output clock signals until after activation of the LOCKED signal. Prior to the activation of the LOCKED signal, the DLL output clocks are not valid and can exhibit glitches, spikes, or other spurious movement.

#### Table 11: Available Library Primitives

Primitive	Port A Width	Port B Width
RAMB4_S4	4	N/A
RAMB4_S4_S4		4
RAMB4_S4_S8		8
RAMB4_54_516		16
RAMB4_S8	8	N/A
RAMB4_S8_S8		8
RAMB4_S8_S16		16
RAMB4_S16	16	N/A
RAMB4_S16_S16		16

# **Port Signals**

Each block RAM port operates independently of the others while accessing the same set of 4096 memory cells.

 Table 12 describes the depth and width aspect ratios for the block RAM memory.

Table 12: Block RAM Port Aspect Ratios

Width	Depth	ADDR Bus	Data Bus
1	4096	ADDR<11:0>	DATA<0>
2	2048	ADDR<10:0>	DATA<1:0>
4	1024	ADDR<9:0>	DATA<3:0>
8	512	ADDR<8:0>	DATA<7:0>
16	256	ADDR<7:0>	DATA<15:0>

# Clock—CLK[A/B]

Each port is fully synchronous with independent clock pins. All port input pins have setup time referenced to the port CLK pin. The data output bus has a clock-to-out time referenced to the CLK pin.

# Enable—EN[A/B]

The enable pin affects the read, write and reset functionality of the port. Ports with an inactive enable pin keep the output pins in the previous state and do not write data to the memory cells.

# Write Enable—WE[A/B]

Activating the write enable pin allows the port to write to the memory cells. When active, the contents of the data input bus are written to the RAM at the address pointed to by the address bus, and the new data also reflects on the data out bus. When inactive, a read operation occurs and the contents of the memory cells referenced by the address bus reflect on the data out bus.

### Reset—RST[A|B]

The reset pin forces the data output bus latches to zero synchronously. This does not affect the memory cells of the RAM and does not disturb a write operation on the other port.

# Address Bus—ADDR[A/B]<#:0>

The address bus selects the memory cells for read or write. The width of the port determines the required width of this bus as shown in Table 12.

## Data In Bus-DI[A/B]<#:0>

The data in bus provides the new data value to be written into the RAM. This bus and the port have the same width, as shown in Table 12.

## Data Output Bus—DO[A/B]<#:0>

The data out bus reflects the contents of the memory cells referenced by the address bus at the last active clock edge. During a write operation, the data out bus reflects the data in bus. The width of this bus equals the width of the port. The allowed widths appear in Table 12.

# **Inverting Control Pins**

The four control pins (CLK, EN, WE and RST) for each port have independent inversion control as a configuration option.

# **Address Mapping**

Each port accesses the same set of 4096 memory cells using an addressing scheme dependent on the width of the port. The physical RAM location addressed for a particular width are described in the following formula (of interest only when the two ports use different aspect ratios).

Table 13 shows low order address mapping for each portwidth.

Table 13: Port Address Mapping

Port Widt h						Ac	P dr	ort es	se	s							
1	4095	1	1	1	1	1	1	0	0	0	0	0	0	0	0	0	0
		5	4	3	2	1	0	9	8	1	6	5	4	3	2	1	0
2	2047	0	07 06			0	5	0	4	0	3	0	2	0	1	0	0
4	1023	03 02 01 00															
8	511	01 00															
16	255								0	0							

# **Creating Larger RAM Structures**

The block RAM columns have specialized routing to allow cascading blocks together with minimal routing delays. This achieves wider or deeper RAM structures with a smaller timing penalty than when using normal routing channels.

# **Location Constraints**

Block RAM instances can have LOC properties attached to them to constrain the placement. The block RAM placement locations are separate from the CLB location naming convention, allowing the LOC properties to transfer easily from array to array.

The LOC properties use the following form:

LOC = RAMB4\_R#C#

RAMB4\_R0C0 is the upper left RAMB4 location on the device.

# **Conflict Resolution**

The block RAM memory is a true dual-read/write port RAM that allows simultaneous access of the same memory cell from both ports. When one port writes to a given memory cell, the other port must not address that memory cell (for a write or a read) within the clock-to-clock setup window. The following lists specifics of port and memory cell write conflict resolution.

- If both ports write to the same memory cell simultaneously, violating the clock-to-clock setup requirement, consider the data stored as invalid.
- If one port attempts a read of the same memory cell the other simultaneously writes, violating the clock-to-clock setup requirement, the following occurs.
  - The write succeeds
  - The data out on the writing port accurately reflects the data written.
  - The data out on the reading port is invalid.

Conflicts do not cause any physical damage.

# Single Port Timing

Figure 33 shows a timing diagram for a single port of a block RAM memory. The block RAM AC switching characteristics are specified in the data sheet. The block RAM memory is initially disabled.

At the first rising edge of the CLK pin, the ADDR, DI, EN, WE, and RST pins are sampled. The EN pin is High and the WE pin is Low indicating a read operation. The DO bus contains the contents of the memory location, 0x00, as indicated by the ADDR bus.

At the second rising edge of the CLK pin, the ADDR, DI, EN, WR, and RST pins are sampled again. The EN and WE pins are High indicating a write operation. The DO bus mirrors

the DI bus. The DI bus is written to the memory location 0x0F.

At the third rising edge of the CLK pin, the ADDR, DI, EN, WR, and RST pins are sampled again. The EN pin is High and the WE pin is Low indicating a read operation. The DO bus contains the contents of the memory location 0x7E as indicated by the ADDR bus.

At the fourth rising edge of the CLK pin, the ADDR, DI, EN, WR, and RST pins are sampled again. The EN pin is Low indicating that the block RAM memory is now disabled. The DO bus retains the last value.

## **Dual Port Timing**

Figure 34 shows a timing diagram for a true dual-port read/write block RAM memory. The clock on port A has a longer period than the clock on Port B. The timing parameter  $T_{BCCS}$ , (clock-to-clock setup) is shown on this diagram. The parameter,  $T_{BCCS}$  is violated once in the diagram. All other timing parameters are identical to the single port version shown in Figure 33.

T<sub>BCCS</sub> is only of importance when the address of both ports are the same and at least one port is performing a write operation. When the clock-to-clock set-up parameter is violated for a WRITE-WRITE condition, the contents of the memory at that location will be invalid. When the clock-to-clock set-up parameter is violated for a WRITE-READ condition, the contents of the memory will be correct, but the read port will have invalid data. At the first rising edge of the CLKA, memory location 0x00 is to be written with the value 0xAAAA and is mirrored on the DOA bus. The last operation of Port B was a read to the same memory location 0x00. The DOB bus of Port B does not change with the new value on Port A, and retains the last read value. A short time later, Port B executes another read to memory location 0x00, and the DOB bus now reflects the new memory value written by Port A.

At the second rising edge of CLKA, memory location 0x7E is written with the value 0x9999 and is mirrored on the DOA bus. Port B then executes a read operation to the same memory location without violating the T<sub>BCCS</sub> parameter and the DOB reflects the new memory values written by Port A.

# SSTL3 Class I

A sample circuit illustrating a valid termination technique for SSTL3\_I appears in Figure 47. DC voltage specifications appear in Table 25 for the SSTL3\_I standard. See "DC Specifications" in Module 3 for the actual FPGA characteristics.

#### SSTL3 Class I



Figure 47: Terminated SSTL3 Class I

Table 2	25:	SSTL3_	I Voltage	Speci	fications
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Parameter	Min	Тур	Max
V <sub>CCO</sub>	3.0	3.3	3.6
$V_{REF} = 0.45 \times V_{CCO}$	1.3	1.5	1.7
$V_{TT} = V_{REF}$	1.3	1.5	1.7
$V_{IH} \ge V_{REF} + 0.2$	1.5	1.7	3.9 <sup>(1)</sup>
$V_{IL} \leq V_{REF} - 0.2$	-0.3(2)	1.3	1.5
$V_{OH} \ge V_{REF} + 0.6$	1.9	-	-
$V_{OL} \leq V_{REF} - 0.6$	-	-	1.1
I <sub>OH</sub> at V <sub>OH</sub> (mA)	-8	-	-
I <sub>OL</sub> at V <sub>OL</sub> (mA)	8	-	-

#### Notes:

1.  $V_{IH}$  maximum is  $V_{CCO}$  + 0.3.

2. V<sub>IL</sub> minimum does not conform to the formula.

## SSTL3 Class II

A sample circuit illustrating a valid termination technique for SSTL3\_II appears in Figure 48. DC voltage specifications appear in Table 26 for the SSTL3\_II standard. See "DC Specifications" in Module 3 for the actual FPGA characteristics.



Figure 48: Terminated SSTL3 Class II

### Table 26: SSTL3\_II Voltage Specifications

Parameter	Min	Тур	Max
V <sub>CCO</sub>	3.0	3.3	3.6
$V_{REF} = 0.45 \times V_{CCO}$	1.3	1.5	1.7
$V_{TT} = V_{REF}$	1.3	1.5	1.7
$V_{IH} \ge V_{REF} + 0.2$	1.5	1.7	3.9 <sup>(1)</sup>
$V_{IL} \leq V_{REF} - 0.2$	-0.3 <sup>(2)</sup>	1.3	1.5
$V_{OH} \ge V_{REF} + 0.8$	2.1	-	-
$V_{OL} \leq V_{REF} - 0.8$	-	-	0.9
I <sub>OH</sub> at V <sub>OH</sub> (mA)	-16	-	-
I <sub>OL</sub> at V <sub>OL</sub> (mA)	16	-	-

Notes:

1.  $V_{IH}$  maximum is  $V_{CCO}$  + 0.3

2. V<sub>IL</sub> minimum does not conform to the formula

## SSTL2\_I

A sample circuit illustrating a valid termination technique for SSTL2\_I appears in Figure 49. DC voltage specifications appear in Table 27 for the SSTL2\_I standard. See "DC Specifications" in Module 3 for the actual FPGA characteristics

#### SSTL2 Class I



Figure 49: Terminated SSTL2 Class I

Table 2	7: SSTL2_	Voltage	Specifications
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Parameter	Min	Тур	Max
V <sub>CCO</sub>	2.3	2.5	2.7
$V_{REF} = 0.5 \times V_{CCO}$	1.15	1.25	1.35
$V_{TT} = V_{REF} + N^{(1)}$	1.11	1.25	1.39
$V_{IH} \ge V_{REF} + 0.18$	1.33	1.43	3.0 <sup>(2)</sup>
$V_{IL} \leq V_{REF} - 0.18$	-0.3 <sup>(3)</sup>	1.07	1.17
V <sub>OH</sub> ≥ V <sub>REF</sub> + 0.61	1.76	-	-
$V_{OL} \le V_{REF} - 0.61$	-	-	0.74
I <sub>OH</sub> at V <sub>OH</sub> (mA)	-7.6	-	-
I <sub>OL</sub> at V <sub>OL</sub> (mA)	7.6	-	-

#### Notes:

- 1. N must be greater than or equal to -0.04 and less than or equal to 0.04.
- 2.  $V_{IH}$  maximum is  $V_{CCO}$  + 0.3.
- 3. V<sub>IL</sub> minimum does not conform to the formula.

## SSTL2 Class II

A sample circuit illustrating a valid termination technique for SSTL2\_II appears in Figure 50. DC voltage specifications appear in Table 28 for the SSTL2\_II standard. See "DC Specifications" in Module 3 for the actual FPGA characteristics.



Figure 50: Terminated SSTL2 Class II

### Table 28: SSTL2\_II Voltage Specifications

Parameter	Min	Тур	Max
V <sub>CCO</sub>	2.3	2.5	2.7
$V_{REF} = 0.5 \times V_{CCO}$	1.15	1.25	1.35
$V_{TT} = V_{REF} + N^{(1)}$	1.11	1.25	1.39
$V_{IH} \ge V_{REF} + 0.18$	1.33	1.43	3.0 <sup>(2)</sup>
$V_{IL} \leq V_{REF} - 0.18$	-0.3 <sup>(3)</sup>	1.07	1.17
$V_{OH} \ge V_{REF} + 0.8$	1.95	-	-
$V_{OL} \leq V_{REF} - 0.8$	-	-	0.55
I <sub>OH</sub> at V <sub>OH</sub> (mA)	-15.2	-	-
I <sub>OL</sub> at V <sub>OL</sub> (mA)	15.2	-	-

#### Notes:

- 1. N must be greater than or equal to -0.04 and less than or equal to 0.04.
- 2.  $V_{IH}$  maximum is  $V_{CCO}$  + 0.3.
- 3. V<sub>IL</sub> minimum does not conform to the formula.

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# LVTTL

LVTTL requires no termination. DC voltage specifications appears in Table 32 for the LVTTL standard. See "DC Specifications" in Module 3 for the actual FPGA characteristics.

Parameter	Min	Тур	Max
V <sub>CCO</sub>	3.0	3.3	3.6
V <sub>REF</sub>	-	-	-
V <sub>TT</sub>	-	-	-
V <sub>IH</sub>	2.0	-	5.5
V <sub>IL</sub>	-0.5	-	0.8
V <sub>OH</sub>	2.4	-	-
V <sub>OL</sub>	-	-	0.4
I <sub>OH</sub> at V <sub>OH</sub> (mA)	-24	-	-
I <sub>OL</sub> at V <sub>OL</sub> (mA)	24	-	-

#### Notes:

1.  $V_{OL}$  and  $V_{OH}$  for lower drive currents sample tested.

## LVCMOS2

LVCMOS2 requires no termination. DC voltage specifications appear in Table 33 for the LVCMOS2 standard. See "DC Specifications" in Module 3 for the actual FPGA characteristics.

### Table 33: LVCMOS2 Voltage Specifications

Parameter	Min	Тур	Max
V <sub>CCO</sub>	2.3	2.5	2.7
V <sub>REF</sub>	-	-	-
V <sub>TT</sub>	-	-	-
V <sub>IH</sub>	1.7	-	5.5
V <sub>IL</sub>	-0.5	-	0.7
V <sub>OH</sub>	1.9	-	-
V <sub>OL</sub>	-	-	0.4
I <sub>OH</sub> at V <sub>OH</sub> (mA)	-12	-	-
I <sub>OL</sub> at V <sub>OL</sub> (mA)	12	-	-

## AGP-2X

The specification for the AGP-2X standard does not document a recommended termination technique. DC voltage specifications appear in Table 34 for the AGP-2X standard. See "DC Specifications" in Module 3 for the actual FPGA characteristics.

## Table 34: AGP-2X Voltage Specifications

Parameter	Min	Тур	Max
V <sub>CCO</sub>	3.0	3.3	3.6
$V_{REF} = N \times V_{CCO}^{(1)}$	1.17	1.32	1.48
V <sub>TT</sub>	-	-	-
$V_{IH} \ge V_{REF} + 0.2$	1.37	1.52	-
$V_{IL} \leq V_{REF} - 0.2$	-	1.12	1.28
$V_{OH} \ge 0.9 \times V_{CCO}$	2.7	3.0	-
$V_{OL} \le 0.1 \times V_{CCO}$	-	0.33	0.36
I <sub>OH</sub> at V <sub>OH</sub> (mA)	Note 2	-	-
I <sub>OL</sub> at V <sub>OL</sub> (mA)	Note 2	-	-

#### Notes:

For design examples and more information on using the I/O, see <u>XAPP179</u>, Using SelectIO Interfaces in Spartan-II and Spartan-IIE FPGAs.

<sup>1.</sup> N must be greater than or equal to 0.39 and less than or equal to 0.41.

<sup>2.</sup> Tested according to the relevant specification.

Input/Output		V <sub>IL</sub>	V	н	V <sub>OL</sub>	V <sub>OH</sub>	I <sub>OL</sub>	I <sub>ОН</sub>
Standard	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
CTT	-0.5	V <sub>REF</sub> – 0.2	V <sub>REF</sub> + 0.2	3.6	V <sub>REF</sub> – 0.4	V <sub>REF</sub> + 0.4	8	-8
AGP	-0.5	V <sub>REF</sub> – 0.2	V <sub>REF</sub> + 0.2	3.6	10% V <sub>CCO</sub>	90% V <sub>CCO</sub>	Note (2)	Note (2)

#### Notes:

1. V<sub>OL</sub> and V<sub>OH</sub> for lower drive currents are sample tested.

2. Tested according to the relevant specifications.

# **Switching Characteristics**

All devices are 100% functionally tested. Internal timing parameters are derived from measuring internal test patterns. Listed below are representative values. For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer (TRCE in the Xilinx Development System) and back-annotated to the simulation netlist. All timing parameters assume worst-case operating conditions (supply voltage and junction temperature). Values apply to all Spartan-II devices unless otherwise noted.

# Global Clock Input to Output Delay for LVTTL, with DLL (Pin-to-Pin)<sup>(1)</sup>

			S	peed Grad	le	
			All	-6	-5	
Symbol	Description	Device	Min	Max	Max	Units
T <sub>ICKOFDLL</sub>	Global clock input to output delay using output flip-flop for LVTTL, 12 mA, fast slew rate, <i>with</i> DLL.	All		2.9	3.3	ns

#### Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.

- Output timing is measured at 1.4V with 35 pF external capacitive load for LVTTL. The 35 pF load does not apply to the Min values. For other I/O standards and different loads, see the tables "Constants for Calculating TIOOP" and "Delay Measurement Methodology," page 60.
- 3. DLL output jitter is already included in the timing calculation.
- 4. For data *output* with different standards, adjust delays with the values shown in "IOB Output Delay Adjustments for Different Standards," page 59. For a global clock input with standards other than LVTTL, adjust delays with values from the "I/O Standard Global Clock Input Adjustments," page 61.

# Global Clock Input to Output Delay for LVTTL, *without* DLL (Pin-to-Pin)<sup>(1)</sup>

			All	-6	-5	
Symbol	Description	Device	Min	Max	Max	Units
T <sub>ICKOF</sub>	T <sub>ICKOF</sub> Global clock input to output delay using output flip-flop for LVTTL, 12 mA, fast slew rate, <i>without</i> DLL.	XC2S15		4.5	5.4	ns
		XC2S30		4.5	5.4	ns
		XC2S50		4.5	5.4	ns
		XC2S100		4.6	5.5	ns
	XC2S150		4.6	5.5	ns	
		XC2S200		4.7	5.6	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.

- Output timing is measured at 1.4V with 35 pF external capacitive load for LVTTL. The 35 pF load does not apply to the Min values. For other I/O standards and different loads, see the tables "Constants for Calculating TIOOP" and "Delay Measurement Methodology," page 60.
- For data *output* with different standards, adjust delays with the values shown in "IOB Output Delay Adjustments for Different Standards," page 59. For a global clock input with standards other than LVTTL, adjust delays with values from the "I/O Standard Global Clock Input Adjustments," page 61.

# **IOB Output Switching Characteristics**

Output delays terminating at a pad are specified for LVTTL with 12 mA drive and fast slew rate. For other standards, adjust the delays with the values shown in "IOB Output Delay Adjustments for Different Standards," page 59.

		Speed Grade				
		-6		-5		
Symbol	Description	Min	Max	Min	Max	Units
Propagation Delays	5					
T <sub>IOOP</sub>	O input to pad	-	2.9	-	3.4	ns
T <sub>IOOLP</sub>	O input to pad via transparent latch	-	3.4	-	4.0	ns
3-state Delays		1				
T <sub>IOTHZ</sub>	T input to pad high-impedance <sup>(1)</sup>	-	2.0	-	2.3	ns
T <sub>IOTON</sub>	T input to valid data on pad	-	3.0	-	3.6	ns
T <sub>IOTLPHZ</sub>	T input to pad high impedance via transparent latch <sup>(1)</sup>	-	2.5	-	2.9	ns
T <sub>IOTLPON</sub>	T input to valid data on pad via transparent latch	-	3.5	-	4.2	ns
T <sub>GTS</sub>	GTS to pad high impedance <sup>(1)</sup>	-	5.0	-	5.9	ns
Sequential Delays		1	I	1		
T <sub>IOCKP</sub>	Clock CLK to pad	-	2.9	-	3.4	ns
Т <sub>ЮСКНZ</sub>	Clock CLK to pad high impedance (synchronous) <sup>(1)</sup>	-	2.3	-	2.7	ns
T <sub>IOCKON</sub>	Clock CLK to valid data on pad (synchronous)	-	3.3	-	4.0	ns
Setup/Hold Times	with Respect to Clock CLK <sup>(2)</sup>	1	l.			
TIOOCK / TIOCKO	O input	1.1/0	-	1.3/0	-	ns
T <sub>IOOCECK</sub> /	OCE input	0.9 / 0.01	-	0.9/0.01	-	ns
TIOCKOCE						
T <sub>IOSRCKO</sub> /	SR input (OFF)	1.2/0	-	1.3 / 0	-	ns
TIOCKOSR				/ -		
TIOTCK / TIOCKT	3-state setup times, T input	0.8/0	-	0.9/0	-	ns
Т <sub>ІОТСЕСК</sub> /	3-state setup times, TCE input	1.0/0	-	1.0/0	-	ns
		11/0		10/0		
	3-state setup times, SK input (TFF)	1.170	-	1.2/0	-	ns
Set/Reset Delays						
	SR input to pad (asynchronous)	_	37	_	44	ns
	SR input to pad high impedance (asynchronous) <sup>(1)</sup>	-	3.1	-	37	ns
	SR input to valid data on pad (asynchronous)	-	4 1	-	49	ns
	GSR to pad	_	9.1	_	11 7	ns
' IOGSRQ	OUN ID Pau	-	9.9	-	11.7	115

Notes:

1. Three-state turn-off delays should not be adjusted.

2. A zero hold time listing indicates no hold time or a negative hold time.

# Calculation of T<sub>IOOP</sub> as a Function of Capacitance

 $T_{\rm IOOP}$  is the propagation delay from the O Input of the IOB to the pad. The values for  $T_{\rm IOOP}$  are based on the standard capacitive load (C<sub>SL</sub>) for each I/O standard as listed in the table "Constants for Calculating TIOOP", below.

For other capacitive loads, use the formulas below to calculate an adjusted propagation delay,  $T_{IOOP1}$ .

$$T_{IOOP1} = T_{IOOP} + Adj + (C_{LOAD} - C_{SL}) * F_{L}$$

Where:

Adj is selected from "IOB Output Delay Adjustments for Different Standards", page 59, according to the I/O standard used

 $C_{\text{LOAD}}\,$  is the capacitive load for the design

F<sub>L</sub> is the capacitance scaling factor

## **Delay Measurement Methodology**

Standard	V <sub>L</sub> (1)	V <sub>H</sub> (1)	Meas. Point	V <sub>REF</sub> Typ <sup>(2)</sup>		
LVTTL	0	3	1.4	-		
LVCMOS2	0	2.5	1.125	-		
PCI33_5	Pe	Per PCI Spec				
PCI33_3	Pe	r PCI Spec		-		
PCI66_3	Pe	-				
GTL	V <sub>REF</sub> – 0.2	V <sub>REF</sub> + 0.2	$V_{REF}$	0.80		
GTL+	V <sub>REF</sub> – 0.2	V <sub>REF</sub> + 0.2	$V_{REF}$	1.0		
HSTL Class I	V <sub>REF</sub> – 0.5	V <sub>REF</sub> + 0.5	$V_{REF}$	0.75		
HSTL Class III	V <sub>REF</sub> – 0.5	V <sub>REF</sub> + 0.5	$V_{REF}$	0.90		
HSTL Class IV	V <sub>REF</sub> – 0.5	V <sub>REF</sub> + 0.5	$V_{REF}$	0.90		
SSTL3 I and II	V <sub>REF</sub> – 1.0	V <sub>REF</sub> + 1.0	$V_{REF}$	1.5		
SSTL2 I and II	$V_{REF} - 0.75$	V <sub>REF</sub> + 0.75	$V_{REF}$	1.25		
CTT	V <sub>REF</sub> – 0.2	V <sub>REF</sub> + 0.2	$V_{REF}$	1.5		
AGP	V <sub>REF</sub> – (0.2xV <sub>CCO</sub> )	V <sub>REF</sub> + (0.2xV <sub>CCO</sub> )	V <sub>REF</sub>	Per AGP Spec		

#### Notes:

- 1. Input waveform switches between V<sub>L</sub> and V<sub>H</sub>.
- 2. Measurements are made at V<sub>REF</sub> Typ, Maximum, and Minimum. Worst-case values are reported.
- I/O parameter measurements are made with the capacitance values shown in the table, "Constants for Calculating TIOOP". See Xilinx application note <u>XAPP179</u> for the appropriate terminations.
- 4. I/O standard measurements are reflected in the IBIS model information except where the IBIS format precludes it.

# Constants for Calculating T<sub>IOOP</sub>

Standard	C <sub>SL</sub> <sup>(1)</sup> (pF)	F <sub>L</sub> (ns/pF)
LVTTL Fast Slew Rate, 2 mA drive	35	0.41
LVTTL Fast Slew Rate, 4 mA drive	35	0.20
LVTTL Fast Slew Rate, 6 mA drive	35	0.13
LVTTL Fast Slew Rate, 8 mA drive	35	0.079
LVTTL Fast Slew Rate, 12 mA drive	35	0.044
LVTTL Fast Slew Rate, 16 mA drive	35	0.043
LVTTL Fast Slew Rate, 24 mA drive	35	0.033
LVTTL Slow Slew Rate, 2 mA drive	35	0.41
LVTTL Slow Slew Rate, 4 mA drive	35	0.20
LVTTL Slow Slew Rate, 6 mA drive	35	0.100
LVTTL Slow Slew Rate, 8 mA drive	35	0.086
LVTTL Slow Slew Rate, 12 mA drive	35	0.058
LVTTL Slow Slew Rate, 16 mA drive	35	0.050
LVTTL Slow Slew Rate, 24 mA drive	35	0.048
LVCMOS2	35	0.041
PCI 33 MHz 5V	50	0.050
PCI 33 MHZ 3.3V	10	0.050
PCI 66 MHz 3.3V	10	0.033
GTL	0	0.014
GTL+	0	0.017
HSTL Class I	20	0.022
HSTL Class III	20	0.016
HSTL Class IV	20	0.014
SSTL2 Class I	30	0.028
SSTL2 Class II	30	0.016
SSTL3 Class I	30	0.029
SSTL3 Class II	30	0.016
СТТ	20	0.035
AGP	10	0.037

#### Notes:

- 1. I/O parameter measurements are made with the capacitance values shown above. See Xilinx application note <u>XAPP179</u> for the appropriate terminations.
- 2. I/O standard measurements are reflected in the IBIS model information except where the IBIS format precludes it.

**Period Tolerance:** the allowed input clock period change in nanoseconds.



**Output Jitter:** the difference between an ideal reference clock edge and the actual design.



Figure 52: Period Tolerance and Clock Jitter

# **CLB Distributed RAM Switching Characteristics**

		Speed Grade				
		-1	6		5	
Symbol	Description	Min	Max	Min	Max	Units
Sequential Dela	ys		·			
Т <sub>SHCKO16</sub>	Clock CLK to X/Y outputs (WE active, 16 x 1 mode)	-	2.2	-	2.6	ns
Т <sub>SHCKO32</sub>	Clock CLK to X/Y outputs (WE active, 32 x 1 mode)	-	2.5	-	3.0	ns
Setup/Hold Time	es with Respect to Clock CLK <sup>(1)</sup>					
T <sub>AS</sub> / T <sub>AH</sub>	F/G address inputs	0.7 / 0	-	0.7 / 0	-	ns
T <sub>DS</sub> / T <sub>DH</sub>	BX/BY data inputs (DIN)	0.8 / 0	-	0.9/0	-	ns
T <sub>WS</sub> / T <sub>WH</sub>	CE input (WS)	0.9/0	-	1.0/0	-	ns
Clock CLK						
T <sub>WPH</sub>	Minimum pulse width, High	-	2.9	-	2.9	ns
T <sub>WPL</sub>	Minimum pulse width, Low	-	2.9	-	2.9	ns
T <sub>WC</sub>	Minimum clock period to meet address write cycle time	-	5.8	-	5.8	ns

Notes:

1. A zero hold time listing indicates no hold time or a negative hold time.

# **CLB Shift Register Switching Characteristics**

		Speed Grade -6 -5				
				5		
Symbol	Description	Min	Max	Min	Max	Units
Sequential Dela	ys					
T <sub>REG</sub>	Clock CLK to X/Y outputs	-	3.47	-	3.88	ns
Setup Times with	th Respect to Clock CLK					
T <sub>SHDICK</sub>	BX/BY data inputs (DIN)	0.8	-	0.9	-	ns
T <sub>SHCECK</sub>	CE input (WS)	0.9	-	1.0	-	ns
Clock CLK						
T <sub>SRPH</sub>	Minimum pulse width, High	-	2.9	-	2.9	ns
T <sub>SRPL</sub>	Minimum pulse width, Low	-	2.9	-	2.9	ns

# **Block RAM Switching Characteristics**

		Speed Grade				
		-6		-5		
Symbol	Description	Min	Max	Min	Max	Units
Sequential Delays		<u>.</u>	<u>.</u>	<u>.</u>	<u>.</u>	<u></u>
Т <sub>ВСКО</sub>	Clock CLK to DOUT output	-	3.4	-	4.0	ns
Setup/Hold Times with Respect to Clock CLK <sup>(1)</sup>						
T <sub>BACK</sub> / T <sub>BCKA</sub>	ADDR inputs	1.4 / 0	-	1.4 / 0	-	ns
T <sub>BDCK</sub> / T <sub>BCKD</sub>	DIN inputs	1.4 / 0	-	1.4 / 0	-	ns
T <sub>BECK</sub> / T <sub>BCKE</sub>	EN inputs	2.9 / 0	-	3.2 / 0	-	ns
T <sub>BRCK</sub> / T <sub>BCKR</sub>	RST input	2.7 / 0	-	2.9/0	-	ns
T <sub>BWCK</sub> / T <sub>BCKW</sub>	WEN input	2.6 / 0	-	2.8 / 0	-	ns
Clock CLK						
T <sub>BPWH</sub>	Minimum pulse width, High	-	1.9	-	1.9	ns
T <sub>BPWL</sub>	Minimum pulse width, Low	-	1.9	-	1.9	ns
T <sub>BCCS</sub>	CLKA -> CLKB setup time for different ports	-	3.0	-	4.0	ns

#### Notes:

1. A zero hold time listing indicates no hold time or a negative hold time.

# **TBUF Switching Characteristics**

		Speed	Speed Grade		
		-6	-5		
Symbol	Description	Max	Max	Units	
Combinatorial Delay	rs			<u>.</u>	
T <sub>IO</sub>	IN input to OUT output	0	0	ns	
T <sub>OFF</sub>	TRI input to OUT output high impedance	0.1	0.2	ns	
T <sub>ON</sub>	TRI input to valid data on OUT output	0.1	0.2	ns	

# **JTAG Test Access Port Switching Characteristics**

		Speed Grade				
		-6		-5		Units
Symbol	Symbol Description		Max	Min Max		
Setup and Hold Time	s with Respect to TCK	· · · · · ·		·		
T <sub>TAPTCK /</sub> T <sub>TCKTAP</sub>	TMS and TDI setup and hold times	4.0/2.0	-	4.0/2.0	-	ns
Sequential Delays		<u> </u>		· · · ·		
T <sub>TCKTDO</sub>	Output delay from clock TCK to output TDO	-	11.0	-	11.0	ns
FTCK	Maximum TCK clock frequency	-	33	-	33	MHz

# **Revision History**

Date	Version No.	Description
09/18/00	2.0	Sectioned the Spartan-II Family data sheet into four modules. Updated timing to reflect the latest speed files. Added current supply numbers and XC2S200 -5 timing numbers. Approved -5 timing numbers as preliminary information with exceptions as noted.
11/02/00	2.1	Removed Power Down feature.
01/19/01	2.2	DC and timing numbers updated to Preliminary for the XC2S50 and XC2S100. Industrial power-on current specifications and -6 DLL timing numbers added. Power-on specification clarified.
03/09/01	2.3	Added note on power sequencing. Clarified power-on current requirement.
08/28/01	2.4	Added -6 preliminary timing. Added typical and industrial standby current numbers. Specified min. power-on current by junction temperature instead of by device type (Commercial vs. Industrial). Eliminated minimum $V_{CCINT}$ ramp time requirement. Removed footnote limiting DLL operation to the Commercial temperature range.
07/26/02	2.5	Clarified that I/O leakage current is specified over the Recommended Operating Conditions for $V_{CCINT}$ and $V_{CCO}$ .
08/26/02	2.6	Added references for XAPP450 to Power-On Current Specification.
09/03/03	2.7	Added relaxed minimum power-on current ( $I_{CCPO}$ ) requirements to page 53. On page 64, moved $T_{RPW}$ values from maximum to minimum column.
06/13/08	2.8	Updated I/O measurement thresholds. Updated description and links. Updated all modules for continuous page, figure, and table numbering. Synchronized all modules to v2.8.

# XC2S100 Device Pinouts (Continued)

XC2S100 Pad Name						Bndry
Function	Bank	TQ144	PQ208	FG256	FG456	Scan
I/O	0	-	P188	A6	C10	107
I/O, V <sub>REF</sub>	0	P12	P189	B7	A9	110
GND	-	-	P190	GND*	GND*	-
I/O	0	-	P191	C8	B9	113
I/O	0	-	P192	D7	E10	116
I/O	0	-	P193	E7	A8	122
I/O	0	-	-	-	D9	125
I/O	0	P11	P194	C7	E9	128
I/O	0	P10	P195	B6	A7	131
V <sub>CCINT</sub>	-	P9	P196	V <sub>CCINT</sub> *	V <sub>CCINT</sub> *	-
V <sub>CCO</sub>	0	-	P197	V <sub>CCO</sub> Bank 0*	V <sub>CCO</sub> Bank 0*	-
GND	-	P8	P198	GND*	GND*	-
I/O	0	P7	P199	A5	B7	134
I/O, V <sub>REF</sub>	0	P6	P200	C6	E8	137
I/O	0	-	-	-	D8	140
I/O	0	-	P201	B5	C7	143
I/O	0	-	-	D6	D7	146
I/O	0	-	P202	A4	D6	152
I/O, V <sub>REF</sub>	0	P5	P203	B4	C6	155
V <sub>CCO</sub>	0	-	-	V <sub>CCO</sub> Bank 0*	V <sub>CCO</sub> Bank 0*	-
GND	-	-	-	GND*	GND*	-
I/O	0	-	P204	E6	B5	158
I/O	0	-	-	D5	E7	161
I/O	0	-	-	-	E6	164
I/O	0	P4	P205	A3	B4	167
I/O	0	-	-	C5	A3	170
I/O	0	P3	P206	B3	C5	176
ТСК	-	P2	P207	C4	C4	-
V <sub>CCO</sub>	0	P1	P208	V <sub>CCO</sub> Bank 0*	V <sub>CCO</sub> Bank 0*	-
V <sub>CCO</sub>	7	P144	P208	V <sub>CCO</sub> Bank 7*	V <sub>CCO</sub> Bank 7*	-

<sup>04/18/01</sup> 

#### Notes:

- 1. IRDY and TRDY can only be accessed when using Xilinx PCI cores.
- Pads labelled GND\*, V<sub>CCINT</sub>\*, V<sub>CCO</sub> Bank 0\*, V<sub>CCO</sub> Bank 1\*, V<sub>CCO</sub> Bank 2\*, V<sub>CCO</sub> Bank 3\*, V<sub>CCO</sub> Bank 4\*, V<sub>CCO</sub> Bank 5\*, V<sub>CCO</sub> Bank 6\*, V<sub>CCO</sub> Bank 7\* are internally bonded to independent ground or power planes within the package.
- 3. See "VCCO Banks" for details on V<sub>CCO</sub> banking.

# XC2S150 Device Pinouts (Continued)

XC2S150 Pad Name					Bndry
Function	Bank	PQ208	FG256	FG456	Scan
I/O	1	P174	B10	C14	72
I/O	1	-	-	B14	75
I/O	1	P175	D10	D13	81
I/O	1	P176	A10	C13	84
GND	-	P177	GND*	GND*	-
V <sub>CCO</sub>	1	-	V <sub>CCO</sub> Bank 1*	V <sub>CCO</sub> Bank 1*	-
I/O, V <sub>REF</sub>	1	P178	B9	B13	87
I/O	1	P179	E10	E12	90
I/O	1	-	A9	B12	93
I/O	1	P180	D9	D12	96
I/O	1	-	-	C12	99
I/O	1	P181	A8	D11	102
I, GCK2	1	P182	C9	A11	108
GND	-	P183	GND*	GND*	-
V <sub>CCO</sub>	1	P184	V <sub>CCO</sub> Bank 1*	V <sub>CCO</sub> Bank 1*	-
V <sub>CCO</sub>	0	P184	V <sub>CCO</sub> Bank 0*	V <sub>CCO</sub> Bank 0*	-
I, GCK3	0	P185	B8	C11	109
V <sub>CCINT</sub>	-	P186	V <sub>CCINT</sub> *	V <sub>CCINT</sub> *	-
I/O	0	-	-	E11	116
I/O	0	P187	A7	A10	119
I/O	0	-	D8	B10	122
I/O	0	P188	A6	C10	125
I/O, V <sub>REF</sub>	0	P189	B7	A9	128
V <sub>CCO</sub>	0	-	V <sub>CCO</sub> Bank 0*	V <sub>CCO</sub> Bank 0*	-
GND	-	P190	GND*	GND*	-
I/O	0	P191	C8	B9	131
I/O	0	P192	D7	E10	134
I/O	0	-	-	D10	140
I/O	0	P193	E7	A8	143
I/O	0	-	-	D9	146
I/O	0	-	-	B8	149
I/O	0	P194	C7	E9	155
I/O	0	P195	B6	A7	158

# XC2S150 Device Pinouts (Continued)

XC2S150 Pad Name					Bndry
Function	Bank	PQ208	FG256	FG456	Scan
V <sub>CCINT</sub>	-	P196	V <sub>CCINT</sub> *	V <sub>CCINT</sub> *	-
V <sub>CCO</sub>	0	P197	V <sub>CCO</sub> Bank 0*	V <sub>CCO</sub> Bank 0*	-
GND	-	P198	GND*	GND*	-
I/O	0	P199	A5	B7	161
I/O, V <sub>REF</sub>	0	P200	C6	E8	164
I/O	0	-	-	D8	167
I/O	0	P201	B5	C7	170
I/O	0	-	D6	D7	173
I/O	0	-	-	B6	176
I/O	0	-	-	A5	179
I/O	0	P202	A4	D6	182
I/O, V <sub>REF</sub>	0	P203	B4	C6	185
V <sub>CCO</sub>	0	-	V <sub>CCO</sub> Bank 0*	V <sub>CCO</sub> Bank 0*	-
GND	-	-	GND*	GND*	-
I/O	0	P204	E6	B5	188
I/O	0	-	D5	E7	191
I/O	0	-	-	A4	194
I/O	0	-	-	E6	197
I/O	0	P205	A3	B4	200
GND	-	-	GND*	GND*	-
I/O	0	-	C5	A3	203
I/O	0	-	-	B3	206
I/O	0	-	-	D5	209
I/O	0	P206	B3	C5	212
ТСК	-	P207	C4	C4	-
V <sub>CCO</sub>	0	P208	V <sub>CCO</sub> Bank 0*	V <sub>CCO</sub> Bank 0*	-
V <sub>CCO</sub>	7	P208	V <sub>CCO</sub> Bank 7*	V <sub>CCO</sub> Bank 7*	-

# 04/18/01 Notes:

- 1. IRDY and TRDY can only be accessed when using Xilinx PCI cores.
- Pads labelled GND\*, V<sub>CCINT</sub>\*, V<sub>CCO</sub> Bank 0\*, V<sub>CCO</sub> Bank 1\*, V<sub>CCO</sub> Bank 2\*, V<sub>CCO</sub> Bank 3\*, V<sub>CCO</sub> Bank 4\*, V<sub>CCO</sub> Bank 5\*, V<sub>CCO</sub> Bank 6\*, V<sub>CCO</sub> Bank 7\* are internally bonded to independent ground or power planes within the package.
- 3. See "VCCO Banks" for details on V<sub>CCO</sub> banking.

# XC2S200 Device Pinouts (Continued)

XC2S200 Pad Name					Bndry
Function	Bank	PQ208	FG256	FG456	Scan
I, GCK0	4	P80	N8	W12	636
I/O	4	P81	N9	U12	640
I/O	4	-	-	V12	646
I/O	4	P82	R9	Y12	649
I/O	4	-	N10	AA12	652
I/O	4	-	-	W13	655
I/O	4	P83	Т9	AB13	661
I/O, V <sub>REF</sub>	4	P84	P9	AA13	664
V <sub>CCO</sub>	4	-	V <sub>CCO</sub> Bank 4*	V <sub>CCO</sub> Bank 4*	-
GND	-	P85	GND*	GND*	-
I/O	4	P86	M10	Y13	667
I/O	4	P87	R10	V13	670
I/O	4	-	-	AB14	673
I/O	4	-	-	W14	676
I/O	4	P88	P10	AA14	679
GND	-	-	GND*	GND*	-
I/O	4	-	-	V14	682
I/O	4	-	-	Y14	685
I/O	4	-	-	W15	688
I/O	4	P89	T10	AB15	691
I/O	4	P90	R11	AA15	694
V <sub>CCINT</sub>	-	P91	V <sub>CCINT</sub> *	V <sub>CCINT</sub> *	-
V <sub>CCO</sub>	4	P92	V <sub>CCO</sub> Bank 4*	V <sub>CCO</sub> Bank 4*	-
GND	-	P93	GND*	GND*	-
I/O	4	P94	M11	Y15	697
I/O, V <sub>REF</sub>	4	P95	T11	AB16	700
I/O	4	-	-	AB17	706
I/O	4	P96	N11	V15	709
GND	-	-	GND*	GND*	-
I/O	4	-	R12	Y16	712
I/O	4	-	-	AA17	715
I/O	4	-	-	W16	718
I/O	4	P97	P11	AB18	721
I/O, V <sub>REF</sub>	4	P98	T12	AB19	724
V <sub>CCO</sub>	4	-	V <sub>CCO</sub> Bank 4*	V <sub>CCO</sub> Bank 4*	-
GND	-	-	GND*	GND*	-
I/O	4	P99	T13	Y17	727
I/O	4	-	N12	V16	730
I/O	4	-	-	AA18	733

# XC2S200 Device Pinouts (Continued)

XC2S200 Pad Name					Bndry
Function	Bank	PQ208	FG256	FG456	Scan
I/O	4	-	-	W17	739
I/O, V <sub>REF</sub>	4	P100	R13	AB20	742
GND	-	-	GND*	GND*	-
I/O	4	-	P12	AA19	745
I/O	4	-	-	V17	748
I/O	4	-	-	Y18	751
I/O	4	P101	P13	AA20	757
I/O	4	P102	T14	W18	760
GND	-	P103	GND*	GND*	-
DONE	3	P104	R14	Y19	763
V <sub>CCO</sub>	4	P105	V <sub>CCO</sub> Bank 4*	V <sub>CCO</sub> Bank 4*	-
V <sub>CCO</sub>	3	P105	V <sub>CCO</sub> Bank 3*	V <sub>CCO</sub> Bank 3*	-
PROGRAM	-	P106	P15	W20	766
I/O (INIT)	3	P107	N15	V19	767
I/O (D7)	3	P108	N14	Y21	770
I/O	3	-	-	V20	776
I/O	3	-	-	AA22	779
I/O	3	-	T15	W21	782
GND	-	-	GND*	GND*	-
I/O, V <sub>REF</sub>	3	P109	M13	U20	785
I/O	3	-	-	U19	788
I/O	3	-	-	V21	794
GND	-	-	GND*	GND*	-
I/O	3	-	R16	T18	797
I/O	3	P110	M14	W22	800
GND	-	-	GND*	GND*	-
V <sub>CCO</sub>	3	-	V <sub>CCO</sub> Bank 3*	V <sub>CCO</sub> Bank 3*	-
I/O, V <sub>REF</sub>	3	P111	L14	U21	803
I/O	3	P112	M15	T20	806
I/O	3	-	-	T19	809
I/O	3	-	-	V22	812
I/O	3	-	L12	T21	815
GND	-	-	GND*	GND*	-
I/O	3	P113	P16	R18	818
I/O	3	-	-	U22	821
I/O, V <sub>REF</sub>	3	P114	L13	R19	827
I/O (D6)	3	P115	N16	T22	830
GND	-	P116	GND*	GND*	-